

## AMENDMENTS TO THE CLAIMS

### Claims 1-169 (Canceled)

170. (currently amended) A semiconductor component comprising:  
a thinned semiconductor ~~die~~ substrate having a circuit side, a back side, four peripheral edges, a plurality of die contacts on the circuit side, and a ~~selected~~ thickness of from  $10\mu\text{m}$  to  ~~$720\mu\text{m}$~~   $152\mu\text{m}$ ;  
a plurality of contact bumps on the die contacts;  
a first polymer layer comprising a continuous layer covering the circuit side and the peripheral edges to the back side, the first polymer layer having a first planar surface on the circuit side and continuous edge polymer layers configured to rigidify the peripheral edges;  
a second polymer layer covering the back side having a second planar surface, the first polymer layer and the second polymer layer encapsulating the ~~die~~ substrate on six sides and supporting the ~~die~~ substrate, the contact bumps and the peripheral edges; and  
a plurality of terminal contacts on the contact bumps.

171. (currently amended) The semiconductor component of claim 170 wherein the ~~die~~ substrate comprises a tested and burned in die and the component comprises a known good component (KGC).

172. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer comprises a thermoset underfill film.

173. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a thermoset underfill film.

174. (withdrawn) The semiconductor component of claim 170 wherein the first polymer layer and the second polymer layer have beveled edges.

175. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer comprises a thermoset underfill film having a cure temperature of about 200-250 °C, a Young's modulus of about 4G Pascal, and a coefficient of thermal expansion (CTE) of about 33 parts per million per °C.

176. (previously presented) The semiconductor component of claim 170 wherein the terminal contacts are arranged in a dense ball grid array (BGA).

177. (currently amended) The semiconductor component of claim 170 wherein the die substrate includes conductive vias in electrical communication with the die contacts and the contact bumps.

178. (previously presented) The semiconductor component of claim 170 wherein the die contacts comprise bond pads.

179. (withdrawn) The semiconductor component of claim 170 wherein the die contacts comprise redistribution pads.

Claims 180-261 (canceled)

262. (previously presented) The semiconductor component of claim 170 wherein the die contacts comprise a solderable metal, and the contact bumps comprise solder.

263. (previously presented) The semiconductor component of claim 170 wherein the terminal contacts and the contact bumps having a height selected to provide a desired spacing for flip chip mounting the component.

264. (previously presented) The semiconductor component of claim 170 wherein the terminal contacts comprise ball bonds on the contact bumps.

265. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer on each edge comprises a portion of a polymer filled trench.

266. (previously presented) The semiconductor component of claim 170 wherein the edge polymer layers and the back side have a same planar surface.

267. (previously presented) The semiconductor component of claim 170 wherein the edge polymer layers have an edge thickness which is different than a thickness of the first polymer layer.

268. (currently amended) The semiconductor component of claim 170 wherein the ~~die~~ substrate comprises a tested and burned in die.

269. (currently amended) The semiconductor component of claim 170 wherein the ~~die~~ substrate is contained on a semiconductor wafer having a polymer support dam proximate to edges thereof.

270. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a thermoset underfill film having a cure temperature of about 200-250 °C, a Young's modulus of about 4G Pascal, and a coefficient of thermal expansion (CTE) of about 33 parts per million per °C.

271. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises parylene.

Claim 272 (canceled)